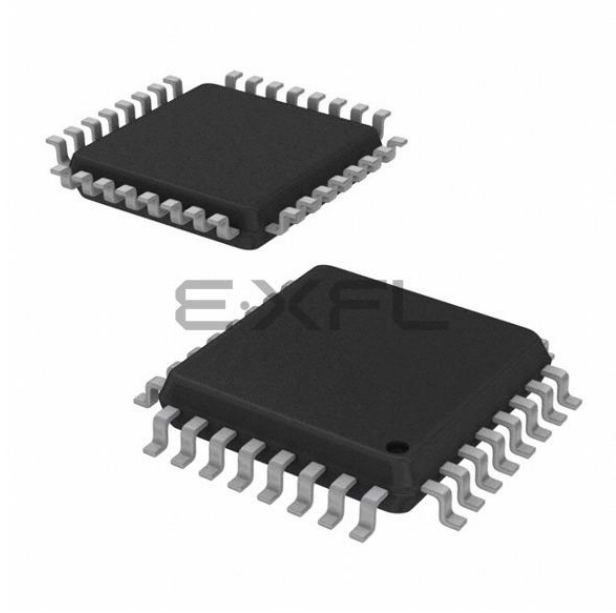

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	25
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 9x12b; D/A 3x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f334k8t6tr

1 Introduction

This datasheet provides the ordering information and the mechanical device characteristics of the STM32F334x4/6/8 microcontrollers.

This document should be read in conjunction with the STM32F303xx reference manual RM0364 available from the STMicroelectronics website *www.st.com*.

For information on the Cortex®-M4 core with FPU, refer to:

- ARM® Cortex®-M4 Processor Technical Reference Manual available from the www.arm.com website.
- STM32F3xxx and STM32F4xxx Cortex®-M4 programming manual (PM0214) available from the *www.st.com* website.

3 Functional overview

3.1 ARM® Cortex®-M4 core with FPU with embedded Flash and SRAM

The ARM Cortex-M4 processor with FPU is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM 32-bit Cortex-M4 RISC processor with FPU features exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allows efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded ARM core, the STM32F334x4/6/8 family is compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the STM32F334x4/6/8 family devices.

3.2 Memories

3.2.1 Embedded Flash memory

All STM32F334x4/6/8 devices feature up to 64 Kbytes of embedded Flash memory available for storing programs and data. The Flash memory access time is adjusted to the CPU clock frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above).

3.2.2 Embedded SRAM

The STM32F334x4/6/8 devices feature up to 12 Kbytes of embedded SRAM with hardware parity check. The memory can be accessed in read/write at CPU clock speed with 0 wait states, allowing the CPU to achieve 90 Dhrystone Mips at 72 MHz when running code from CCM (core coupled memory) RAM.

The SRAM is organized as follows:

- 4 Kbytes of SRAM on instruction and data bus with parity check (core coupled memory or CCM) and used to execute critical routines or to access data
- 12 Kbytes of SRAM with parity check mapped on the data bus.

3.2.3 Boot modes

At startup, BOOT0 pin and BOOT1 option bit are used to select one of the three boot options:

- Boot from user Flash memory
- Boot from System Memory
- Boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART2 (PA2/PA3), I2C1 (PB6/PB7).

3.3 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.4 Power management

3.4.1 Power supply schemes

- V_{SS}, V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. It is provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supply for ADC, DACs, comparators operational amplifiers, reset blocks, RCs and PLL.The minimum voltage to be applied to V_{DDA} differs from one analog peripherals to another. See the *Table 3* below, summarizing the V_{DDA} ranges for analog peripherals. The V_{DDA} voltage level must be always greater or equal to the V_{DD} voltage level and must be provided first.
- V_{DD18} = 1.65 to 1.95 V (V_{DD18} domain): power supply for digital core, SRAM and Flash memory. V_{DD18} is internally generated through an internal voltage regulator.

Table 3. V_{DDA} ranges for analog peripherals

Analog peripheral	Min V_{DDA}supply	Max V_{DDA}supply
ADC/COMP	2 V	3.6 V
DAC/OPAMP	2.4 V	3.6 V

- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.4.2 Power supply supervisor

The device has an integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device

3.13 Ultra-fast comparators (COMP)

The STM32F334x4/6/8 devices embed three ultra-fast rail-to-rail comparators (COMP2/4/6) which offer the features below:

- Programmable internal or external reference voltage
- Selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output
- Internal reference voltage or submultiple (1/4, 1/2, 3/4). Refer to *Table 23: Embedded internal reference voltage* for values and parameters of the internal reference voltage.

All comparators can wake up from STOP mode, generate interrupts and breaks for the timers.

3.14 Timers and watchdogs

The STM32F334x4/6/8 includes advanced control timer, 5 general-purpose timers, basic timer, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Table 5. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare Channels	Complementary outputs
High-resolution timer	HRTIM1(1)	16-bit	Up	/1 /2 /4 (x2 x4 x8 x16 x32, with DLL)	Yes	10	Yes
Advanced control	TIM1(1)	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	Yes
General-purpose	TIM2	32-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM3	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

1. TIM1 can be clocked from the PLL x 2 running at 144 MHz .

3.14.1 217 ps high-resolution timer (HRTIM1)

The high-resolution timer (HRTIM1) allows generating digital signals with high-accuracy timings, such as PWM or phase-shifted pulses.

It consists of 6 timers, 1 master and 5 slaves, totaling 10 high-resolution outputs, which can be coupled by pairs for deadtime insertion. It also features 5 fault inputs for protection purposes and 10 inputs to handle external events such as current limitation, zero voltage or zero current switching.

HRTIM1 timer is made of a digital kernel clocked at 144 MHz followed by delay lines. Delay lines with closed loop control guarantee a 217 ps resolution whatever the voltage, temperature or chip-to-chip manufacturing process deviation. The high-resolution is available on the 10 outputs in all operating modes: variable duty cycle, variable frequency, and constant ON time.

The slave timers can be combined to control multiswitch complex converters or operate independently to manage multiple independent converters.

The waveforms are defined by a combination of user-defined timings and external events such as analog or digital feedbacks signals.

HRTIM1 timer includes options for blanking and filtering out spurious events or faults. It also offers specific modes and features to offload the CPU: DMA requests, burst mode controller, push-pull and resonant mode.

It supports many topologies including LLC, Full bridge phase shifted, buck or boost converters, either in voltage or current mode, as well as lighting application (fluorescent or LED). It can also be used as a general purpose timer, for instance to achieve high-resolution PWM-emulated DAC.

In debug mode, the HRTIM1 counters can be frozen and the PWM outputs enter safe state.

3.14.2 Advanced timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIM timers (described in *Section 3.14.3* using the same architecture, so the advanced-control timers can work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

3.14.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

3.15 Real-time clock (RTC) and backup registers

The RTC and the 5 backup registers are supplied through a switch that takes power from either the V_{DD} supply when present or the VBAT pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present.

They are not reset by a system or power reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms with wake up from Stop and Standby mode capability.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy.
- Two anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.
- 17-bit Auto-reload counter for periodic interrupt with wakeup from STOP/STANDBY capability.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 40 kHz)
- The high-speed external clock divided by 32.

4 Pinout and pin descriptions

Figure 4. LQFP32 pinout

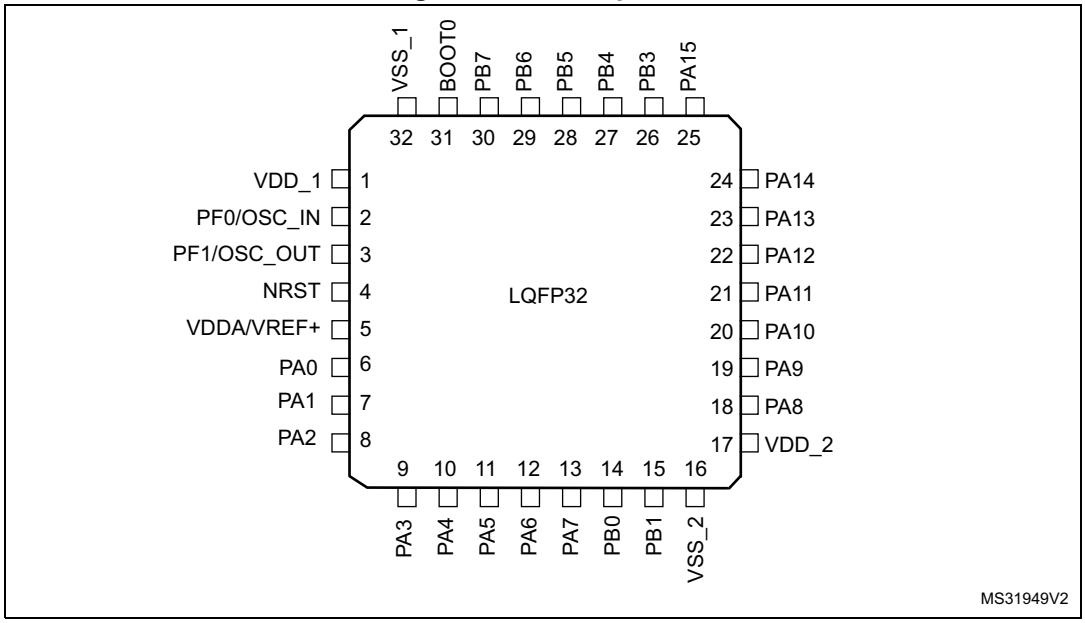
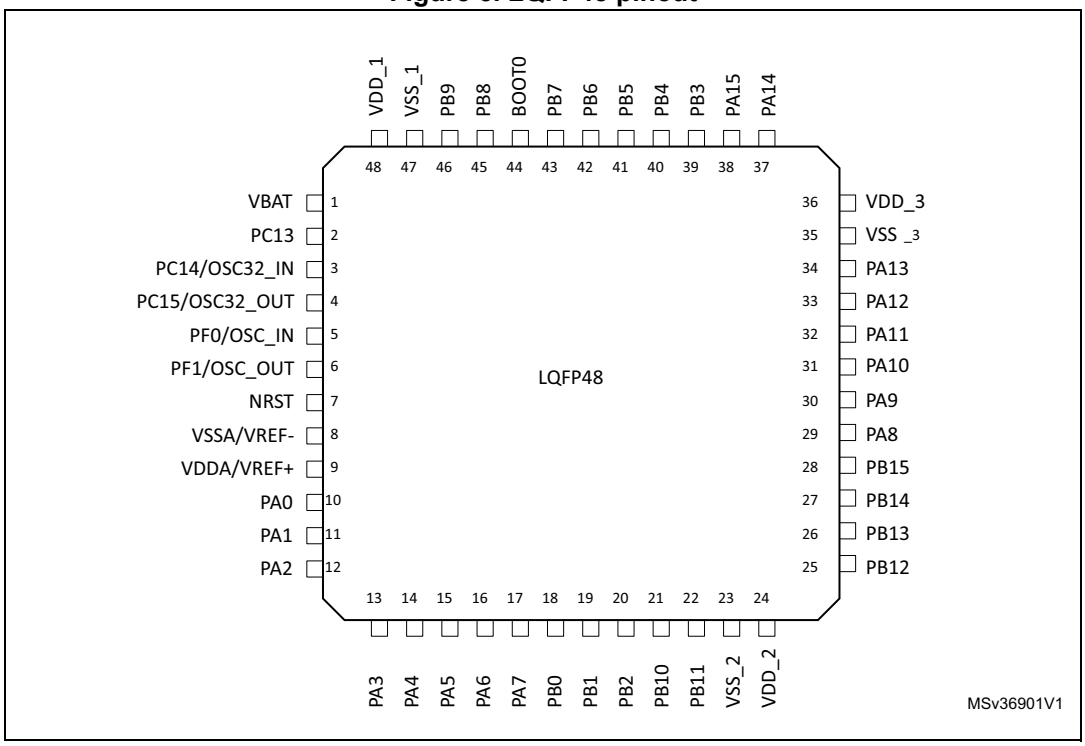


Figure 5. LQFP48 pinout



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3 σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V, V_{DDA} = 3.3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 8*.

6.1.5 Input voltage on a pin

The input voltage measurement on a pin of the device is described in *Figure 9*.

Figure 8. Pin loading conditions

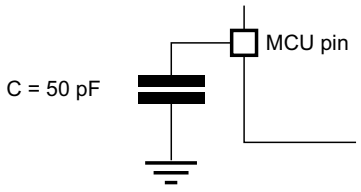
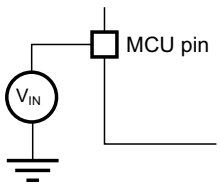


Figure 9. Pin input voltage



6.3 Operating conditions

6.3.1 General operating conditions

Table 19. General operating conditions

Symbol	Parameter	Conditions	Min.	Max.	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	72	
V_{DD}	Standard operating voltage	-	2	3.6	V
V_{DD18}	Core, SRAM and Flash memory power supply	-	1.65	1.95	
V_{DDA}	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to or higher than V_{DD}	2	3.6	
	Analog operating voltage (OPAMP and DAC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.65	3.6	V
V_{IN}	I/O input voltage	TC I/O	–0.3	V_{DD}+0.3	V
		TT I/O	-0.3	3.6	
		TTa I/O	–0.3	V_{DDA}+0.3	
		FT and FTf I/O(1)	–0.3	5.5	
		BOOT0	0	5.5	
PD	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP64	-	444	mW
PD	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP48	-	364	mW
PD	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7	LQFP32	-	333	mW
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	85	°C
		Low power dissipation(3)	–40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	°C
		Low power dissipation(3)	–40	125	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	125	

1. To sustain a voltage higher than V_{DD}+0.3 V, the internal pull-up/pull-down resistors must be disabled.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see *Section Table 78.: Package thermal characteristics*).
3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 20* are derived from tests performed under the ambient temperature condition summarized in *Table 19*.

Table 20. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min.	Max.	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Characteristics of the embedded reset and power-control block

The parameters given in *Table 21* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 19*.

Table 21. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{POR/PDR}$(1)	Power on/power down reset threshold	Falling edge	1.8(2)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}$(3)	POR reset temporization	-	1.5	2.5	4.5	ms

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
3. Guaranteed by design, not tested in production.

Table 25. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6V

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ.	Max. @ T_A(1)			Typ.	Max. @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, executing from Flash	External clock (HSE bypass)	72 MHz	71.4	77.9	79.1	80.0	27.1	32.2	32.4	32.4	mA
			64 MHz	63.9	70.6	71.3	71.5	24.2	27.0	27.5	27.7	
			48 MHz	49.5	56.6	57.1	57.7	18.7	21.4	21.6	21.9	
			32 MHz	34.0	38.6	38.9	39.2	12.9	14.6	14.9	15.9	
			24 MHz	25.9	30.2	30.4	30.6	10.0	11.1	11.2	12.3	
			8 MHz	9.3	14.1	14.3	14.4	3.3	4.0	4.4	5.1	
			1 MHz	3.5	8.9	9.1	9.5	0.7	0.9	1.0	1.2	
		Internal clock (HSI)	64 MHz	61.6	68.1	68.8	70.1	24.1	27.0	27.1	27.2	
			48 MHz	48.1	54.6	54.8	55.1	18.6	21.6	21.7	21.9	
			32 MHz	33.3	37.8	37.9	38.0	12.7	14.4	14.9	16.0	
			24 MHz	25.7	29.8	29.8	30.0	10.0	11.1	11.2	12.3	
			8 MHz	9.7	12.2	12.3	12.8	3.4	3.8	4.2	5.0	
	Supply current in Run mode, executing from RAM	External clock (HSE bypass)	72 MHz	71.3	77.8(2)	78.7	78.9(2)	27.6	32.1(2)	32.2	32.3(2)	
			64 MHz	63.8	70.5	70.7	70.9	24.5	27.2	27.6	27.7	
			48 MHz	49.3	56.5	56.9	57.4	18.1	21.6	21.8	21.8	
			32 MHz	33.9	37.7	37.9	38.0	12.9	14.9	14.9	15.9	
			24 MHz	25.8	28.8	29.0	29.2	9.8	11.1	11.3	11.5	
			8 MHz	9.0	13.2	13.3	13.8	3.2	3.6	4.0	4.6	
			1 MHz	3.2	7.6	7.8	8.0	0.3	0.4	0.8	1.2	
		Internal clock (HSI)	64 MHz	61.3	66.9	67.3	67.8	24.1	26.9	27.0	27.1	
			48 MHz	48.0	52.4	52.6	53.1	19.1	21.6	21.6	22.1	
			32 MHz	33.1	35.6	35.8	36.6	12.6	14.8	14.9	15.9	
			24 MHz	25.6	28.5	28.7	28.8	9.8	11.1	11.3	11.5	
			8 MHz	9.7	11.6	11.6	11.7	3.0	3.1	4.1	4.7	
I_{DD}	Supply current in Sleep mode, executing from Flash or RAM	External clock (HSE bypass)	72 MHz	55.5	58.7(2)	61.1	61.9(2)	7.0	7.3(2)	8.4	8.5(2)	mA
			64 MHz	49.8	52.7	54.5	54.8	6.3	6.7	7.0	7.8	
			48 MHz	38.5	40.6	41.7	41.8	4.6	5.1	5.6	5.9	
			32 MHz	26.9	28.8	29.2	29.5	3.0	3.3	4.0	4.5	
			24 MHz	19.1	23.2	23.7	23.9	2.4	2.5	3.2	3.8	
			8 MHz	7.1	11.5	11.7	11.9	0.6	0.9	1.2	2.1	
			1 MHz	3.0	7.4	7.7	7.9	0.3	0.3	0.4	1.2	
		Internal clock (HSI)	64 MHz	47.7	52.4	52.6	52.8	5.4	6.5	6.8	7.5	
			48 MHz	35.0	40.4	40.6	40.8	4.3	4.7	5.2	5.7	
			32 MHz	23.7	27.7	28.3	28.8	2.9	3.1	3.2	4.4	
			24 MHz	18.5	23.8	24.0	24.2	1.3	1.7	2.2	2.7	
			8 MHz	7.5	9.6	9.7	9.7	0.5	0.7	1.1	2.0	

1. Data based on characterization results, not tested in production unless otherwise specified.
2. Data based on characterization results and tested in production with code executing from RAM.

Table 31. Typical current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Typ.		Unit
				Peripherals enabled	Peripherals disabled	
I_{DD}	Supply current in Sleep mode from V_{DD} supply	Running from HSE crystal clock 8 MHz, code executing from Flash or RAM	72 MHz	51.8	6.3	mA
			64 MHz	46.4	5.7	
			48 MHz	35.0	4.40	
			32 MHz	23.7	3.13	
			24 MHz	18.0	2.49	
			16 MHz	12.2	1.85	
			8 MHz	6.2	0.99	
			4 MHz	3.68	0.88	
			2 MHz	2.26	0.80	
			1 MHz	1.55	0.76	
			500 kHz	1.20	0.74	
			125 kHz	0.89	0.72	
I_{DDA} (1) (2)	Supply current in Sleep mode from V_{DDA} supply		72 MHz	239.0	236.7	µA
			64 MHz	209.4	207.8	
			48 MHz	154.0	152.9	
			32 MHz	103.7	103.2	
			24 MHz	80.1	79.8	
			16 MHz	56.7	56.6	
			8 MHz	1.14	1.14	
			4 MHz	1.14	1.14	
			2 MHz	1.14	1.14	
			1 MHz	1.14	1.14	
			500 kHz	1.14	1.14	
			125 kHz	1.14	1.14	

1. V_{DDA} supervisor is OFF.
2. When peripherals are enabled, the power consumption of the analog part of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

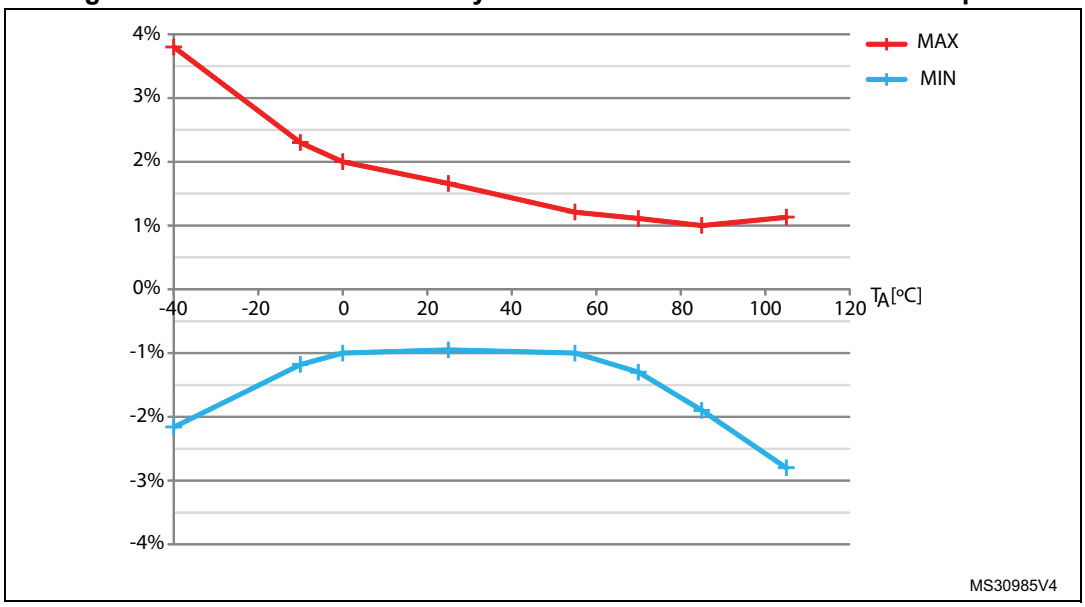
I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 50: I/O static characteristics*.

Figure 17. HSI oscillator accuracy characterization results for soldered parts



Low-speed internal (LSI) RC oscillator

Table 41. LSI oscillator characteristics(1)

Symbol	Parameter	Min.	Typ.	Max.	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DD(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 42* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 19*.

Table 42. PLL characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
f_{PLL_IN}	PLL input clock(1)	1(2)	-	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	72	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
Jitter	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design, not tested in production.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence or oscillator frequency deviation). The test results are given in *Table 49: I/O current injection susceptibility*.

Table 49. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	– 0	NA	mA
	Injected current on PC0, PC1, PC2, PC3 (TTa pins) and PF1 pin (FT pin)	-0	+5	
	Injected current on PA0, PA1, PA2, PA3, PA4, PA5, PA6, PA7, PC4, PC5, PB0, PB1, PB2, PB12, PB13, PB14, PB15 with induced leakage current on other pins from this group less than -100 µA or more than +900 µA	-5	+5	
	Injected current on PB11, other TT, FT, and FTf pins	– 5	NA	
	Injected current on all other TC, TTa and RESET pins	– 5	+5	

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 19*. All I/Os are CMOS and TTL compliant.

Table 50. I/O static characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{IL}	Low level input voltage	TT, TC and TTa I/O	-	-	$0.3\ V_{DD}+0.07$ (1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DD}-0.2$ (1)	
		BOOT0	-	-	$0.3\ V_{DD}–0.3$ (1)	
		All I/Os except BOOT0	-	-	$0.3\ V_{DD}$ (2)	
V_{IH}	High level input voltage	TTa and TT I/O	$0.445\ V_{DD}+0.398$ (1)	-	-	
		FT and FTf I/O	$0.5\ V_{DD+0.2}$ (1)	-	-	
		BOOT0	$0.2\ V_{DD}+0.95$ (1)	-	-	
		All I/Os except BOOT0	$0.7\ V_{DD}$ (2)	-	-	

Table 66. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Conditions			Min (3)	Typ	Max (3)	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz Sampling freq. ≤ 5 Msps V_{DDA} = 3.3 V 25°C	Single ended	Fast channel 5.1 Ms	-	±4	±4.5	LSB
				Slow channel 4.8 Ms	-	±5.5	±6	
			Differential	Fast channel 5.1 Ms	-	±3.5	±4	
				Slow channel 4.8 Ms	-	±3.5	±4	
EO	Offset error		Single ended	Fast channel 5.1 Ms	-	±2	±2	
				Slow channel 4.8 Ms	-	±1.5	±2	
			Differential	Fast channel 5.1 Ms	-	±1.5	±2	
				Slow channel 4.8 Ms	-	±1.5	±2	
EG	Gain error		Single ended	Fast channel 5.1 Ms	-	±3	±4	
				Slow channel 4.8 Ms	-	±5	±5.5	
			Differential	Fast channel 5.1 Ms	-	±3	±3	
				Slow channel 4.8 Ms	-	±3	±3.5	
ED	Differential linearity error		Single ended	Fast channel 5.1 Ms	-	±1	±1	
				Slow channel 4.8 Ms	-	±1	±1	
			Differential	Fast channel 5.1 Ms	-	±1	±1	
				Slow channel 4.8 Ms	-	±1	±1	
EL	Integral linearity error		Single ended	Fast channel 5.1 Ms	-	±1.5	±2	
				Slow channel 4.8 Ms	-	±2	±3	
			Differential	Fast channel 5.1 Ms	-	±1.5	±1.5	
				Slow channel 4.8 Ms	-	±1.5	±2	
ENOB (4)	Effective number of bits		Single ended	Fast channel 5.1 Ms	10.8	10.8	-	bit
				Slow channel 4.8 Ms	10.8	10.8	-	
			Differential	Fast channel 5.1 Ms	11.2	11.3	-	
				Slow channel 4.8 Ms	11.2	11.3	-	
SINAD (4)	Signal-to-noise and distortion ratio		Single ended	Fast channel 5.1 Ms	66	67	-	dB
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	

Table 68. ADC accuracy(1)(2) at 1MSPS

Symbol	Parameter	Test conditions		Typ	Max(3)	Unit
ET	Total unadjusted error	ADC Freq ≤ 72 MHz Sampling Freq ≤ 1MSPS 2.4 V ≤ V_{DDA} = V_{REF+} ≤ 3.6 V Single-ended mode	Fast channel	±2.5	±5	LSB
			Slow channel	±3.5	±5	
EO	Offset error		Fast channel	±1	±2.5	
			Slow channel	±1.5	±2.5	
EG	Gain error		Fast channel	±2	±3	
			Slow channel	±3	±4	
ED	Differential linearity error		Fast channel	±0.7	± 2	
			Slow channel	±0.7	±2	
EL	Integral linearity error		Fast channel	±1	±3	
			Slow channel	±1.2	±3	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.. Any positive injection current within the limits specified for IINJ(PIN) and ∑IINJ(PIN) in *Section 6.3.14: I/O port characteristics* does not affect the ADC accuracy.
3. Data based on characterization results, not tested in production.

Figure 28. ADC accuracy characteristics

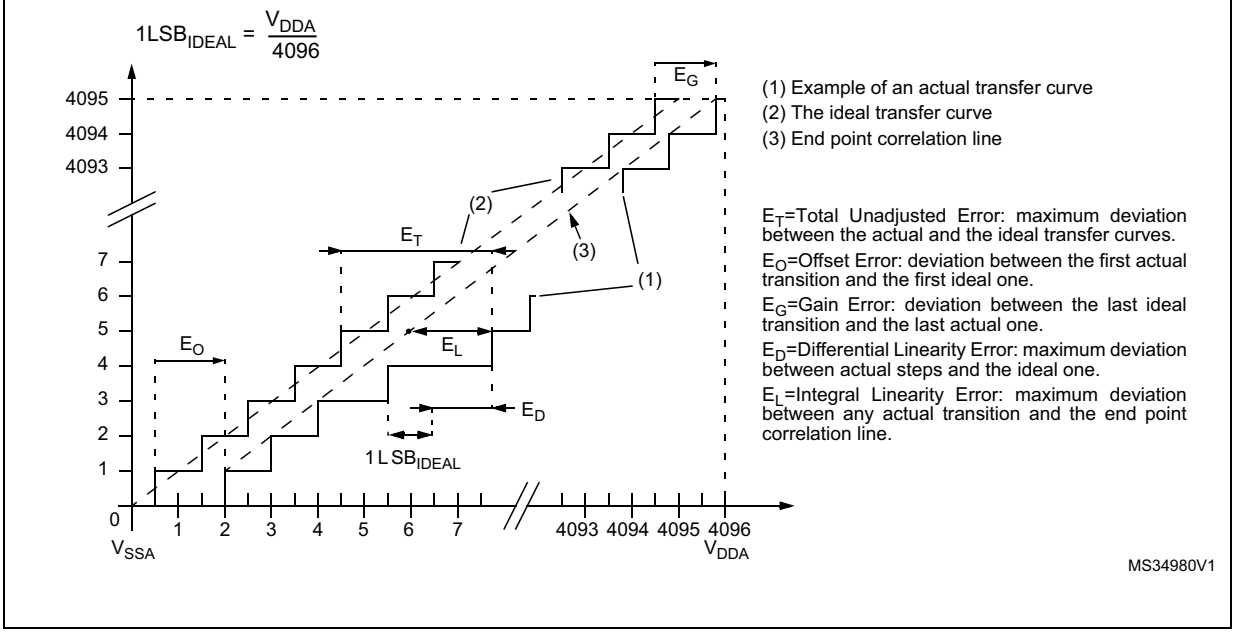
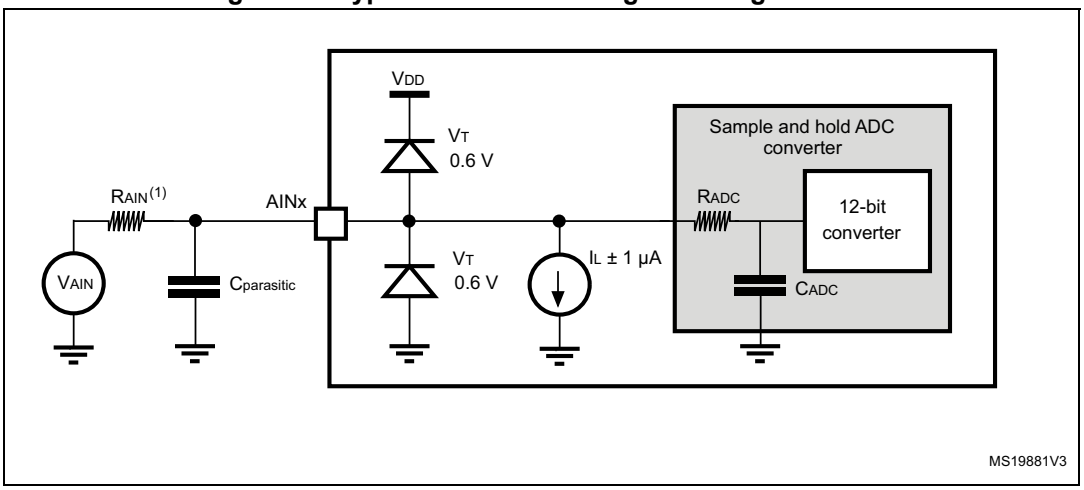


Figure 29. Typical connection diagram using the ADC



1. Refer to *Table 64* for the values of R_{AIN}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 10: Power-supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.20 DAC electrical specifications

Table 69. DAC characteristics

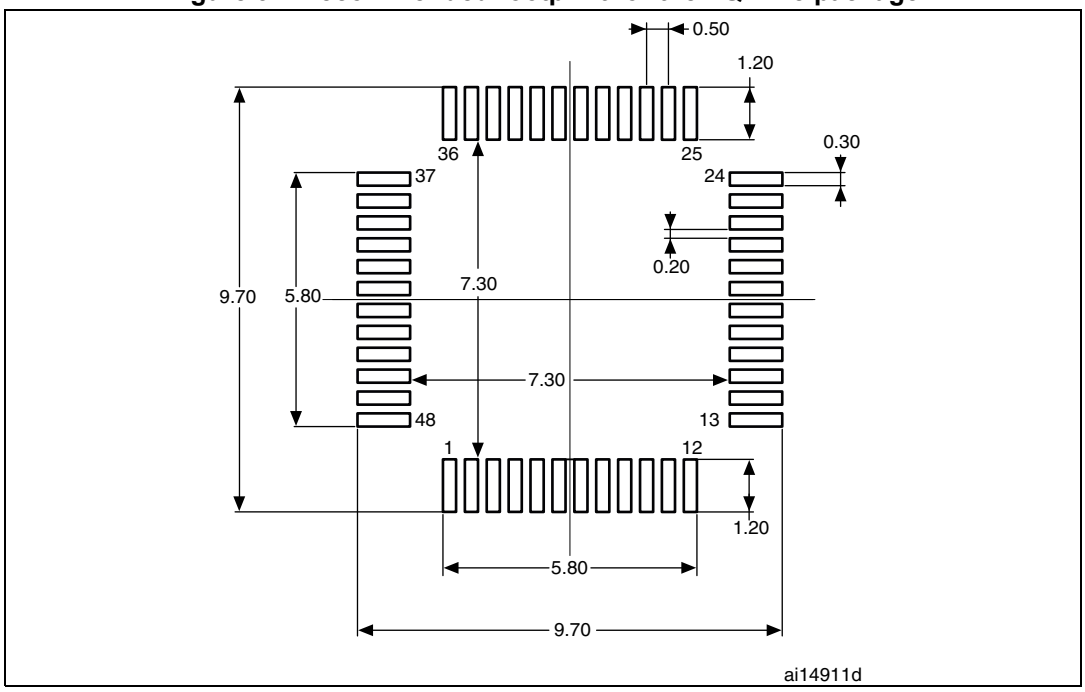
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DDA}	Analog supply voltage	-	2.4	-	3.6	V
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{SSA})	5	-	-	kΩ
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{DDA})	25	-	-	kΩ
R_O(1)	Output impedance	DAC output buffer OFF	-	-	15	kΩ
C_{LOAD}(1)	Capacitive load	DAC output buffer ON	-	-	50	pF
V_{DAC_OUT}(1)	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V	0.2	-	V_{DDA} – 0.2	V
		DAC output buffer OFF	-	0.5	-	mV
			-	-	V_{DDA}– 1LSB	V
I_{DDA}(3)	DAC DC current consumption in quiescent mode(2)	With no load, middle code (0x800) on the input	-	-	380	µA
		With no load, worst code (0xF1C) on the input.	-	-	480	µA

Table 76. LQFP48 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-		0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 37. Recommended footprint for the LQFP48 package



1. Drawing is not to scale.
2. Dimensions are in millimeters.

9 Revision history

Table 80. Document revision history

Date	Revision	Changes
19-Jun-2014	1	Initial release.
09-Dec-2014	2	Updated: *Table 54: TIMx characteristics* *Table 14: STM32F303x6/8 pin definitions* *Table 59: ADC characteristics* *Table 34: Peripheral current consumption* *Table 40: HSI oscillator characteristics* *Table 17: HSI oscillator accuracy characterization results for soldered parts* *Table 2: STM32F334x4/6/8 family device features and peripheral counts*
2-Feb-2015	3	Updated: *Figure 1: STM32F334x4/6/8 block diagram* *Table 38: HSE oscillator characteristics* *Table 43: Flash memory characteristics* Added *Figure 13: High-speed external clock source AC timing diagram*
09-Jun-2015	4	Udpated : Title *Section 3.14.1: 217 ps high-resolution timer (HRTIM1)* *Section 6.1.6: Power-supply scheme* *Table 19: General operating conditions*
27-Sep-2016	5	Updated: *Section Table 69.: DAC characteristics*, *Section Table 64.: ADC characteristics*,*Table 53: NRST pin characteristics*, *Figure 2: Clock tree*,*Table 13: STM32F334x4/6/8 pin definitions*, *Table 71: Operational amplifier characteristics*, *Figure 20: Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port*, *Table 23: Embedded internal reference voltage*, *Table 39: LSE oscillator characteristics (fLSE = 32.768 kHz)* Added: *Table 35: Wakeup time using USART*